

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 62-077479

(43)Date of publication of application : 09.04.1987

(51)Int.Cl.

C23C 16/50

(21)Application number : 60-218755

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(22)Date of filing : 30.09.1985

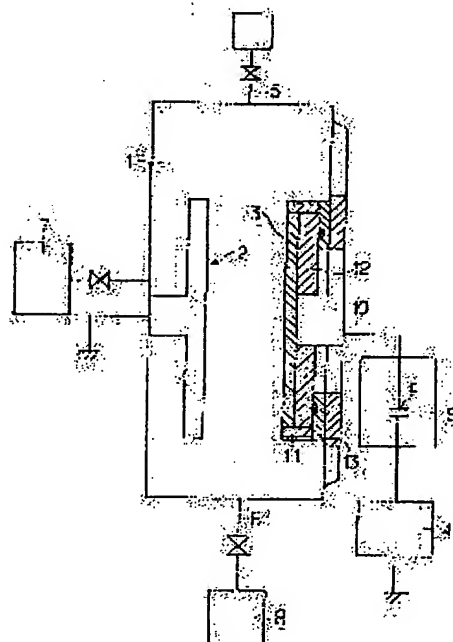
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(54) FORMATION OF THIN FILM BY PLASMA CVD METHOD

(57)Abstract:

PURPOSE: To reduce ion bombardment time and to improve the quality of a thin film by disposing an earth electrode plate and discharge electrode plate to face each other in a vacuum chamber and impressing a square wave high-frequency voltage between both electrodes.

CONSTITUTION: The earth electrode plate 2 and the discharge electrode plate 3 are disposed to face each other in the vacuum chamber 1. The discharge electrode plate 3 is connected to a high-frequency power source 4 via a capacitor C for impedance matching. After the inside of the vacuum chamber 1 is evacuated by a high vacuum evacuation section 8, a reactive gas is introduced from a reactive gas introducing part 5 into the chamber and is discharged from a reactive gas discharge part 8. The partial pressure of the reactive gas is adjusted. The square high-frequency voltage is impressed between the two electrodes 2 and 3 to generate a glow discharge between the electrode plates 2, 3 and a substrate for film formation. The ion bombardment time by cations is thereby reduced and the film of the deposited layer having the improved quality is formed on the discharge.



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[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other
than the examiner's decision of rejection or
application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's
decision of rejection]

[Date of requesting appeal against
examiner's decision of rejection]

[Date of extinction of right]

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